

SAH
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3-12-02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION: GEUN-YOUNG YEOM, ET. AL.

FOR: METHOD OF ETCHING SEMICONDUCTOR DEVICE USING NEUTRAL BEAM AND APPARATUS FOR ETCHING THE SAME

AMENDMENT

The Assistant Commissioner of
Patents and Trademarks
Washington, DC 20231

Dear Sir:

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"Express Mail" mailing label numberDate of Deposit November 8, 2001

I hereby certify that this paper or fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to the Commissioner of Patents and Trademarks, Washington, D.C. 20231.

Jennifer Motson

(Typed or printed name of person mailing paper or fee)

Jennifer Motson
(Signature of person mailing paper or fee)

Before examining the present application, please preliminarily amend the specification, claims and abstract as follows:

IN THE CLAIMS

Please replace claims 1-13 with the following rewritten versions:

A
1. (Amended) A method of etching a semiconductor device using a neutral beam comprising:

extracting an ion beam having a predetermined polarity from an ion source to accelerate the ion beam;

reflecting an accelerated ion beam by a reflector to neutralize the reflected ion beam; and

positioning a substrate to be etched in a path of a neutral beam to etch a material layer on the substrate with the neutral beam.